

QNERC Workshop on Nano Devices and Materials

Tuesday, 4<sup>th</sup> November, 2014

Conference Room 605, Ookayama South-9, Tokyo Institute of Technology

- 10:00 – 10:10     Shunri Oda/ TIT                    Welcome Address
- 10:10 – 10:40     Simon Deleonibus/CEA-LETI, Towards full 3D, zero variability and  
zero power future micro/nano-electronics.
- 10:40 – 11:05     Ken Uchida/ Keio U. Thermal-aware device design of advanced  
nanoscale electronic devices
- 11:05 – 11:30     Hiroshi Wakabayashi TIT, TBA
- 11:30 – 11:55     Hiroshi Mizuta/ JAIST, Downscaled graphene nanoelectronic and  
nano-electro-mechanical (NEM) devices
- (Lunch Break)
- 13:00 – 13:25     Mutsuko Hatano/ TIT, TBA
- 13:25 – 13:50     Mohamed Boutchich/ U. Paris, Characterization of doped epitaxial  
graphene grown on SiC(0001)
- 13:50 – 14:15     Chuanbo Li/ IoS-CAS, [Si/Ge nanomaterials and their device  
application](#)
- 14:15 – 14:40     Marolop D. K. Simanullang/ TIT, Synthesis, passivation, and  
characterisation of germanium nanowires
- 14:40 – 15:05     Zhengyu Xu/ TIT, Impact of gold catalyst evolution on Ge nanowire  
morphologies
- (Coffee Break)
- 15:25 – 15:50     Buwen Cheng/ IoS-CAS, [Toward Group-IV Laser for Integrated Silicon  
Photonics. Presenter](#)
- 15:50 – 16:15     Tetsuo Kodaera/ TIT, Quantum devices using group IV materials
- 16:15 – 16:40     Jaime Oscar Tenorio Pearl/ Cambridge/TIT, Coherent control of a  
trapped electron in a disordered dielectric.
- 16:40 – 17:05     David Herbschleb/ Cambridge/TIT, Charge-writing induced quantum  
devices in graphene.
- 17:05 – 17:30     Chunlai Xue/ IoS-CAS, [Si based Ge and GeSn photodetectors for  
optical communication and data center](#)
- 17:30 – 17:55     Yukio Kawano/ TIT, Nano-Carbon Devices as an Enabler of Terahertz  
Technology